# 500 V, 0.5 A NPN high-voltage low VCEsat transistor 16 March 2022 Product da

**Product data sheet** 

### 1. General description

NPN high-voltage low  $V_{CEsat}$  transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package. PNP complement: PBHV9040T-Q.

#### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain (h<sub>FE</sub>) at high collector current
- Small SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- · LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	400	V
I <sub>C</sub>	collector current		-	-	0.5	Α
h <sub>FE</sub>	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	100	200	-	



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## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		В —
				E
			1 2	sym021
			SOT23	

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBHV8540T-Q		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBHV8540T-Q	W4%

[1] % = placeholder for manufacturing site code

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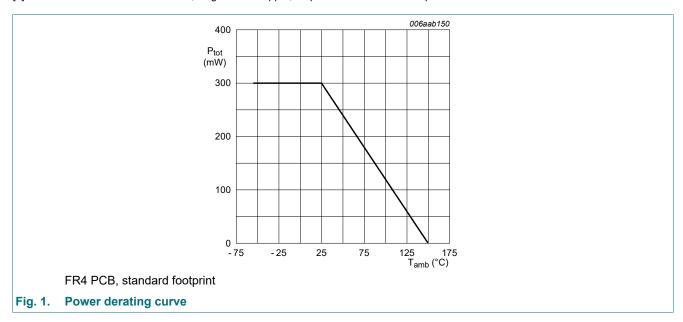
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	500	V
$V_{CEO}$	collector-emitter voltage	open base		-	400	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	500	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	0.5	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1	Α
I <sub>BM</sub>	peak base current			-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



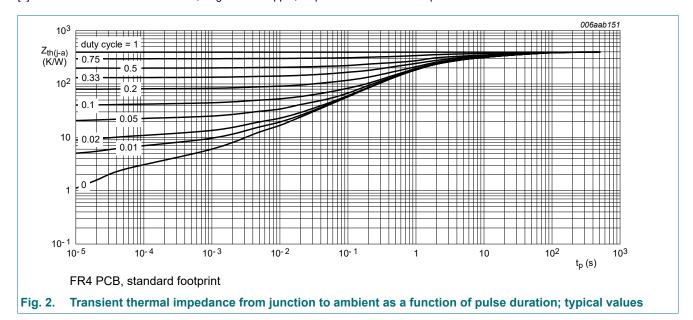
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#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 320 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 320 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 320 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
ЕВО	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	200	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; T <sub>amb</sub> = 25 °C	80	150	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 300 mA; pulsed; $t_{p} \le$ 300 μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	10	20	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	100	200	mV
		I <sub>C</sub> = 100 mA; I <sub>B</sub> = 20 mA; T <sub>amb</sub> = 25 °C	-	60	90	mV
		I <sub>C</sub> = 300 mA; I <sub>B</sub> = 60 mA; T <sub>amb</sub> = 25 °C	-	135	250	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 300 mA; $I_B$ = 60 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	0.91	1.1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	50	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	6200	-	ns
t <sub>on</sub>	turn-on time		-	6250	-	ns
t <sub>s</sub>	storage time		-	800	-	ns
t <sub>f</sub>	fall time		-	2200	-	ns
t <sub>off</sub>	turn-off time		-	3000	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	30	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	4	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	165	-	pF

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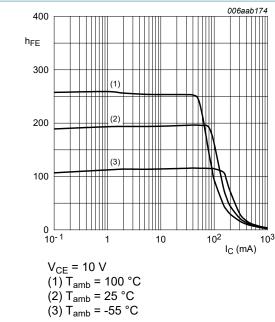


Fig. 3. DC current gain as a function of collector current; typical values

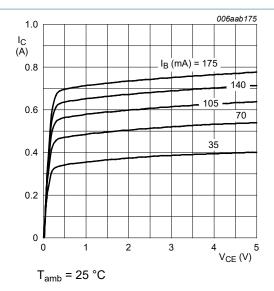
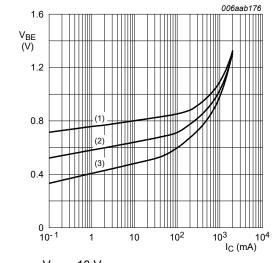


Fig. 4. Collector current as a function of collectoremitter voltage; typical values



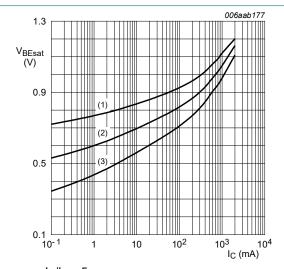
 $V_{CE}$  = 10 V

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 5$ 

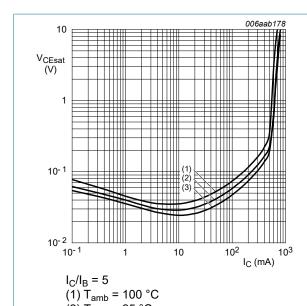
(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

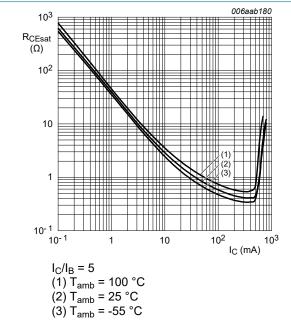


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

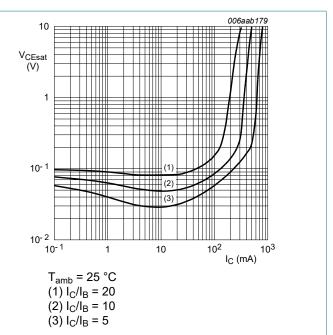


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

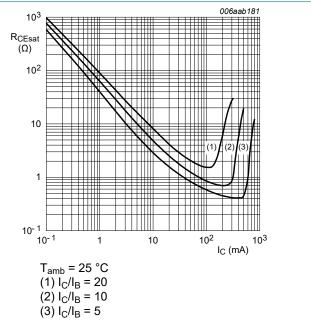
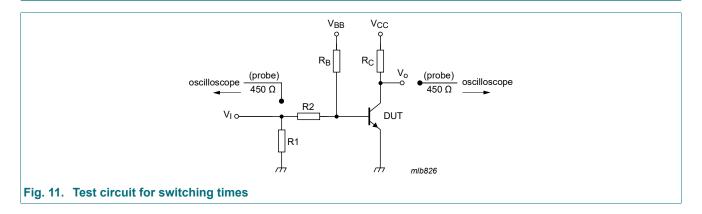


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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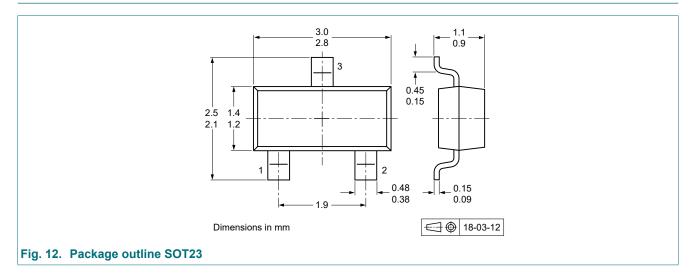
## 11. Test information



#### **Quality information**

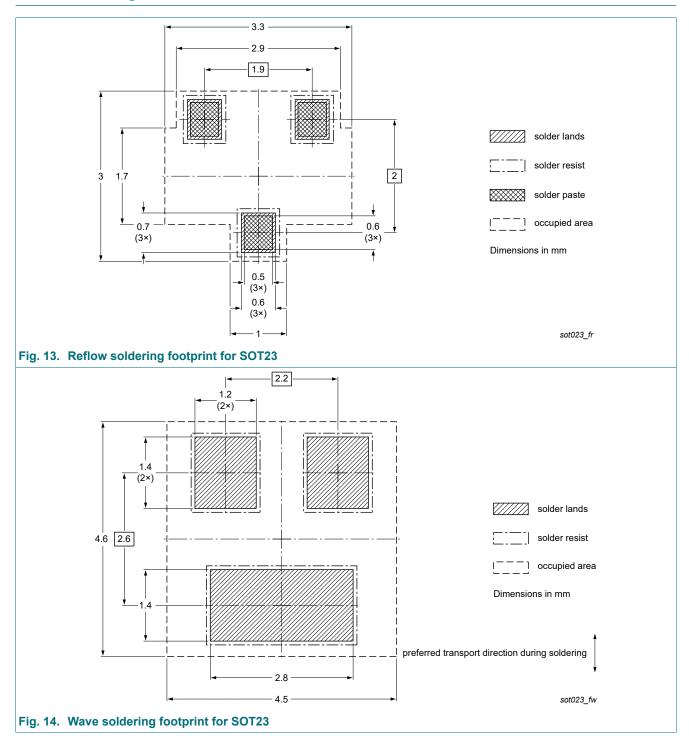
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



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## 13. Soldering



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## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8540T-Q v.1	20220316	Product data sheet	-	-

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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